## UNISONIC TECHNOLOGIES CO., LTD

### **UTG40N135LSS1**

**Preliminary** 

Insulated Gate Bipolar Transistor

# 1350V, SMPS N-CHANNEL IGBT

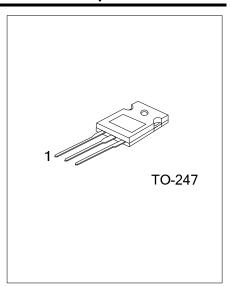
#### DESCRIPTION

The UTC **UTG40N135LSS1** is a N-channel IGBT. it uses UTC's advanced technology to provide customers with high input impedance, high switching speed and low conduction loss, etc.

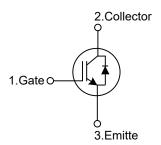
The UTC **UTG40N135LSS1** is suitable for high voltage switching, high frequency switch mode power supplies.

#### ■ FEATURES

- \* High switching speed
- \* High avalanche ruggedness
- \* Low saturation voltage:  $V_{CE(SAT).Typ.} = 1.78V @ I_C=40A$ ,  $V_{GE}=15V (T_C=25^{\circ}C)$



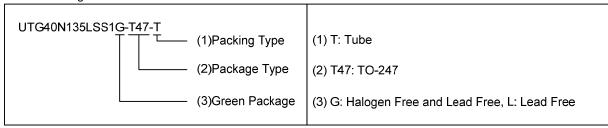
#### ■ SYMBOL



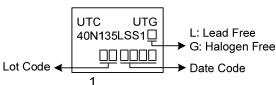
#### ORDERING INFORMATION

Ordering Number		Daalaaaa	Pin Assignment			Dli	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG40N135LSS1L-T47-T	UTG40N135LSS1G-T47-T	TO-247	G	С	Е	Tube	

Note: Pin Assignment: G: Gate C: Collector E: Emitter



#### ■ MARKING



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#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Emitter Voltage		V <sub>CES</sub>	1350	V	
Gate-Emitter Voltage		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	±20	V	
Transient Gate-Emitter Voltage (tp < 5 ms)		$V_{GES}$	±25	V	
Continuous Collector Current	T <sub>C</sub> =25°C	Ic	80	Α	
	T <sub>C</sub> =100°C		40	Α	
Collector Current Pulsed (Note 1)		I <sub>CM</sub>	160	Α	
Diode Forward Current	T <sub>C</sub> =25°C	I <sub>F</sub>	80	Α	
	T <sub>C</sub> =100°C		40	Α	
Short Circuit Withstand Time		tsc			
$V_{\rm GE} = 15 \text{V}, \ V_{\rm CC} \le 200 \text{V}$				μs	
Allowed number of short circuits < 1000			3		
Time between short circuits: ≥ 1.0s					
$T_{VJ} = 25^{\circ}\text{C}$					
Power Dissipation (T <sub>C</sub> =25°C)		$P_{D}$	285	W	
Operating Junction Temperature		$T_J$	-40 ~ +150	°C	
Storage Temperature Range		T <sub>STG</sub>	-55 ~ +150	°C	

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

#### ■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT	
Junction to Case	0.10	0.44	°C/W	

<sup>2.</sup> Pulse width limited by maximum junction temperature.

### ■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise specified)

		T		ı	1	1	r
PARAMETER	SYMBOL	TEST CONDITI	TEST CONDITIONS		TYP	MAX	UNIT
Off Characteristics							
Collector-Emitter Breakdown Voltage	$BV_CES$			1350			V
Collector Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =1350V, V <sub>GE</sub> =0V				5	μΑ
G-E Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V				±400	nA
On Characteristics							
Gate to Emitter Threshold Voltage	$V_{\text{GE(TH)}}$	I <sub>C</sub> =250μA, V <sub>CE</sub> =V <sub>GE</sub>		4.0		7.0	V
Collector to Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =40A, V <sub>GE</sub> =15V	T <sub>C</sub> =25°C		1.78	2.3	V
			T <sub>C</sub> =125°C		2.2		V
Dynamic Characteristics							
Input Capacitance	C <sub>IES</sub>	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V, f=1MHz			3450		pF
Output Capacitance	C <sub>OES</sub>				151		рF
Reverse Transfer Capacitance	C <sub>RES</sub>				51		рF
Switching Characteristics							
Total Gate Charge	$Q_{\mathrm{G}}$				148		nC
Gate-Emitter Charge	$Q_{GE}$	V <sub>CE</sub> =600V, I <sub>C</sub> =40A, V <sub>GE</sub> =15V			36		nC
Gate-Collector Charge	Q <sub>GC</sub>				70		nC
Turn-On Delay Time	t <sub>DON)</sub>				21		ns
Rise Time	t <sub>R</sub>				39		ns
Turn-Off Delay Time	t <sub>DOFF)</sub>	V <sub>CC</sub> =600V, I <sub>C</sub> =40A, R <sub>G</sub> =5Ω, V <sub>GE</sub> =0~15V, L=500μH			103		ns
Fall Time	t <sub>F</sub>				211		ns
Turn-On Switching Loss	Eon				3.14		mJ
Turn-Off Switching Loss	E <sub>OFF</sub>			2.52		mJ	
SOURCE- DRAIN DIODE RATINGS A		TERISTICS		•	•	•	
Forward Voltage Drop	VF	I <sub>F</sub> =40A				3.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =40A, dI/dt=100A/μS, V <sub>CC</sub> =400V			60		ns
Reverse Recovery Charge	Qrr				2.62		μC
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#### ■ TEST CIRCUIT AND WAVEFORMS

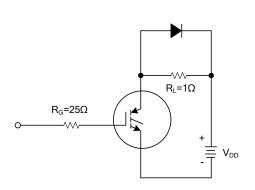


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

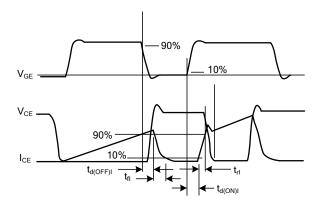


Fig 2. SWITCHING TEST WAVEFORMS

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